

## AMENDMENTS TO THE CLAIMS ARE AS FOLLOWS:

What is claimed is:

1. (PREVIOUSLY PRESENTED). A method of forming a semiconductor device, the steps comprising:

forming a silicon dioxide layer on a semiconductor substrate;

forming a silicon nitride layer on said silicon dioxide layer;

forming isolation trench regions in said semiconductor substrate;

removing said silicon nitride layer;

first implantation of dopant through said silicon dioxide to form sacrificial implanted silicon dioxide layer;

second implantation of dopant through said sacrificial implanted silicon dioxide layer to form wells; and

removing said sacrificial implanted silicon dioxide layer and forming a gate dielectric layer over said semiconductor substrate.

2. (CURRENTLY AMENDED). The method of forming a semiconductor device according to claim 1, wherein said silicon dioxide layer thickness is approximately about 25 Å - 120 Å.

3. (PREVIOUSLY PRESENTED). The method of forming a semiconductor device according to claim 1, wherein said first implanted dopant comprises n- or p- type ions.

4. (PREVIOUSLY PRESENTED). The method of forming a semiconductor device according to claim 3, wherein said first implanted n- type dopant is As<sup>+</sup> or P<sup>+</sup> ion.

5. (PREVIOUSLY PRESENTED). The method of forming a semiconductor device according to claim 4, wherein said As<sup>+</sup> dopant implantation energy, dose, and tilt angle are approximately about 2 – 7 keV, 3E11 – 7E11 ions/cm<sup>2</sup>, and 5 – 10 degrees of tilt angle respectively; and for P<sup>+</sup> ion, implant energy, dose and tilt angle are approximately about 2 – 15 keV, 3E11 – 7E11 ions/cm<sup>2</sup>, and 5 – 10 degrees respectively.

6. (PREVIOUSLY PRESENTED). The method of forming a semiconductor device according to claim 1, wherein said second implanted dopant comprises n- or p- type ions.

7. (PREVIOUSLY PRESENTED). The method of forming a semiconductor device according to claim 6, wherein said second implanted n- type dopant is As<sup>+</sup> or P<sup>+</sup> ion.

8. (PREVIOUSLY PRESENTED). The method of forming a semiconductor device according to claim 7, wherein said second As<sup>+</sup> or P<sup>+</sup> ion dopant implantation energy, dose, and tilt angle are approximately about 80 – 140 keV, 1E13 – 2E13 ions/cm<sup>2</sup>, and 0 – 15 degrees of tilt angle respectively.

9. (PREVIOUSLY PRESENTED). A method of forming a semiconductor device, the steps comprising:

forming a silicon dioxide layer on a silicon substrate;

forming a silicon nitride layer on said silicon dioxide layer;

forming isolation trench regions in said silicon substrate and removing said silicon nitride;

first implantation of  $\text{As}^+$  dopant through said silicon dioxide layer to form sacrificial implanted silicon dioxide layer;

second implantation of  $\text{As}^+$  dopant through said sacrificial implanted silicon dioxide layer to form wells; and

removing said sacrificial implanted silicon dioxide layer and forming a gate dielectric layer over said silicon substrate.

10. (PREVIOUSLY PRESENTED). The method of forming a semiconductor device according to claim 9, wherein said silicon dioxide layer thickness is approximately about 25 Å - 120 Å.

11. (PREVIOUSLY PRESENTED). The method of forming a semiconductor device according to claim 9, wherein said first implanted  $\text{As}^+$  dopant implantation energy, dose, and tilt angle are approximately about 2-7 keV,  $3\text{E}11$ –  $7\text{E}11$  ions/cm<sup>2</sup>, and 5 – 10 degrees of tilt angle respectively.

12. (PREVIOUSLY PRESENTED). The method of forming a semiconductor device according to claim 9, wherein said second implanted  $\text{As}^+$  dopant implantation energy, dose, and tilt angle are approximately about 80 - 140 keV,  $1\text{E}13$  –  $2\text{E}13$  ions/cm<sup>2</sup>, and 0 - 15 degrees of tilt angle respectively.

13. (PREVIOUSLY PRESENTED). A method of forming a semiconductor device with improved threshold voltage stability, the steps comprising:

forming isolation trenches in a silicon substrate with steps comprising: forming silicon nitride over silicon dioxide stack on said silicon substrate; and selective removal of said silicon nitride;

forming a sacrificial implanted silicon dioxide layer by implanting first  $\text{As}^+$  ions into said silicon dioxide layer;

forming n- well in silicon substrate by second implantation of  $\text{As}^+$  ions through said sacrificial implanted silicon dioxide layer; and

removing said sacrificial implanted silicon dioxide layer and forming a gate dielectric layer over said silicon substrate.

14. (PREVIOUSLY PRESENTED). The method of forming a semiconductor device according to claim 13, wherein said silicon dioxide layer thickness is approximately about 25 Å - 120 Å.

15. (PREVIOUSLY PRESENTED). The method of forming a semiconductor device according to claim 13, wherein said first implanted  $\text{As}^+$  dopant implantation energy, ion dose, and tilt angle are approximately about 2 - 7 keV,  $3\text{E}11 - 7\text{E}11$  ions/cm<sup>2</sup>, and 5 – 10 degrees of tilt angle respectively.

16. (PREVIOUSLY PRESENTED). The method of forming a semiconductor device according to claim 13, wherein said second implanted  $\text{As}^+$  dopant implantation energy, dose, and

tilt angle are approximately about 80 - 140 keV,  $1\text{E}13 - 2\text{E}13$  ions/cm<sup>2</sup>, and 0 - 15 degrees of tilt angle respectively.